

Supporting Information

Tribovoltaic Effect Promotes Highly Efficient Direct-Current Generator

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Table S1. The open-circuit voltage of different type TENGs based on dynamic Schottky contact

Materials	Open-circuit voltage (V)	Reference
Graphene/Si	0.22	1
Stainless steel/Si	0.02	2
Carbon Aerogel/Si	2	3
Al/PEDOT:PSS	1	4
Al/CsPbBr ₃	3.69	5

Table S2. The power density of different type TENGs based on dynamic Schottky contact

Materials	Power density (mW/m ²)	Reference
Al foil/PEDOT:PSS	1.1	6
Al alloy/PEDOT:PSS	11.67	4
Stainless steel/Si	0.15	2
Graphene/Si	50	1
Carbon Aerogel/Si	61	3
Steel ball/Si	3.7	7

Table S3. The short-circuit current and current density of different type

TENGs based on dynamic Schottky contact

Contact types	Materials	Short-circuit current (μA)	Current density (A/m^2)	Reference
Block	Al alloy/PEDOT:PSS	309	/	4
	Al foil/PEDOT:PSS	2.5	0.025	6
	Carbon Aerogel/Si	15	100	3
	Cu-G/Si	45	0.775	8
	MXene/Si	22	/	9
	Graphene/Si	4	40	1
	Stainless steel/Si	20	/	2
AFM tip	Pt/MoS ₂	0.001	10 ⁶	10
	Graphite/Si	0.003	210	11
Needle	W/WO ₃	1.2E-4	1270	12
Micro Area	Steel ball/Si	0.03	/	7
	Al/CsPbBr ₃	6	11.46	5

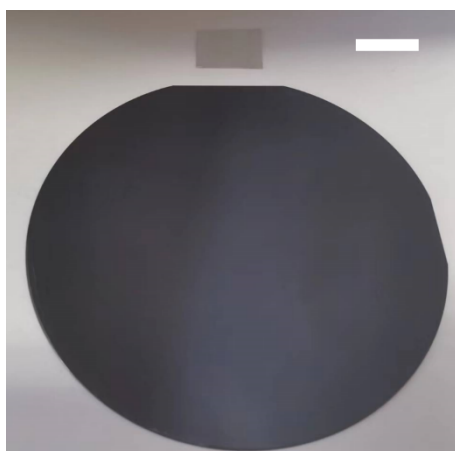


Figure S1. A detailed photograph of Al foil and P-Si with PVP on its

surface (scale bar, 10 mm).

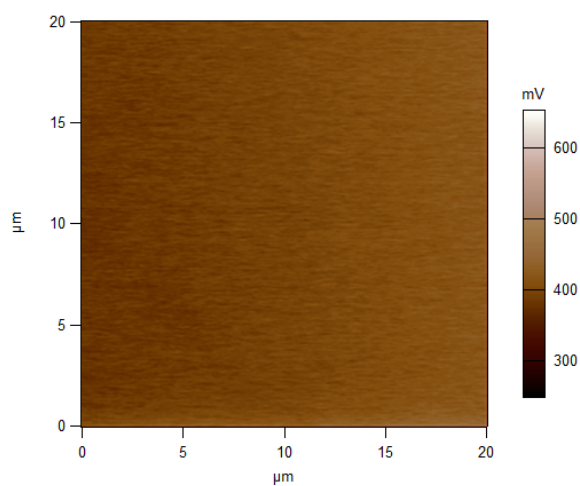


Figure S2. The surface potential of p-Si by the atomic force microscope.

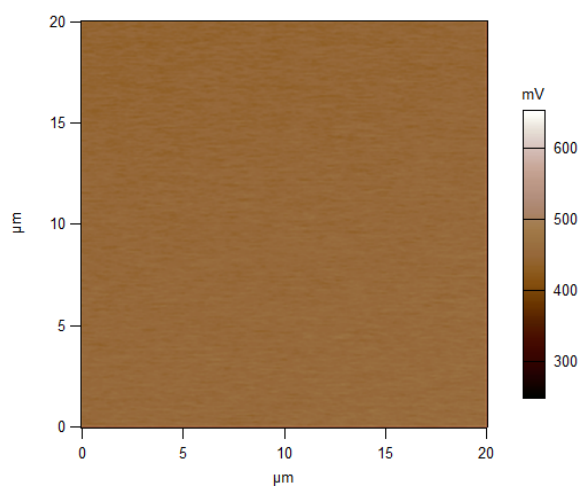


Figure S3. The surface potential of p-Si with PVP on surface by the
atomic force microscope.

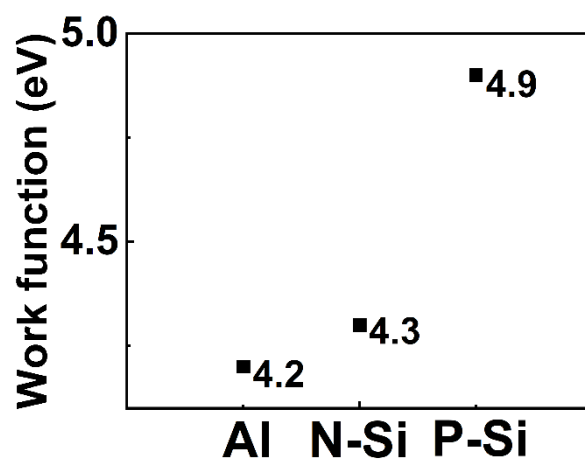


Figure S4. Work function of friction materials.

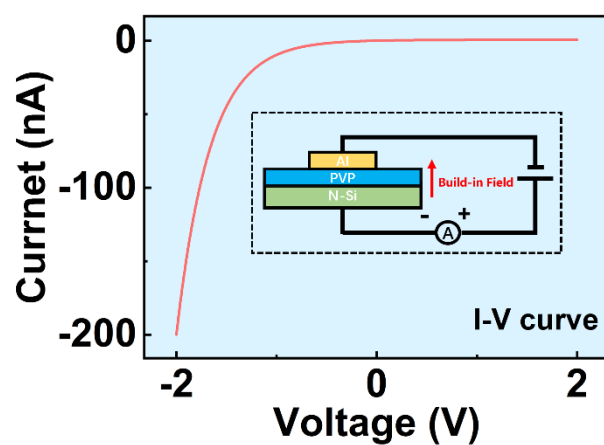


Figure S5. I–V characteristic of the MPS-TENG (n-Si).

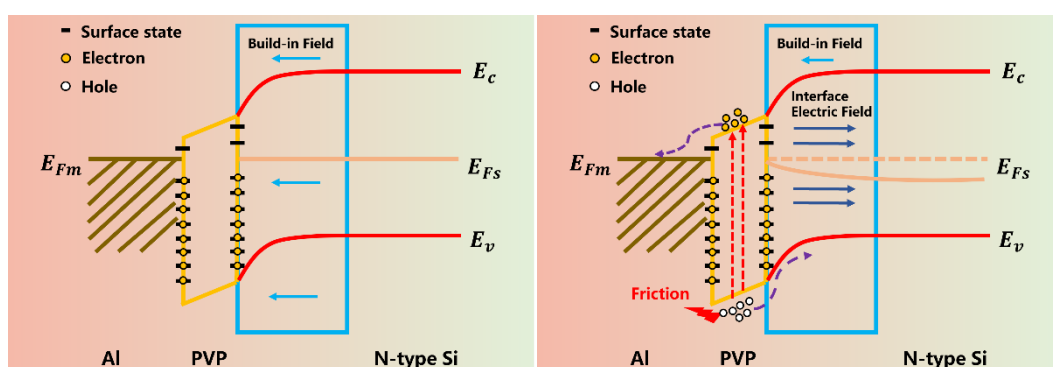


Figure S6. Energy band diagram of the MPS-TENG (n-Si) in static (left) and dynamic (right) states.

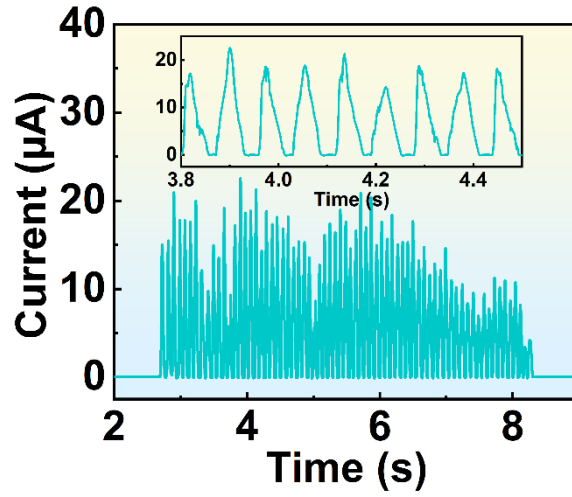


Figure S7. Short-circuit current of the MPS-TENG (p-Si). Inset: Partial magnified view of the current.

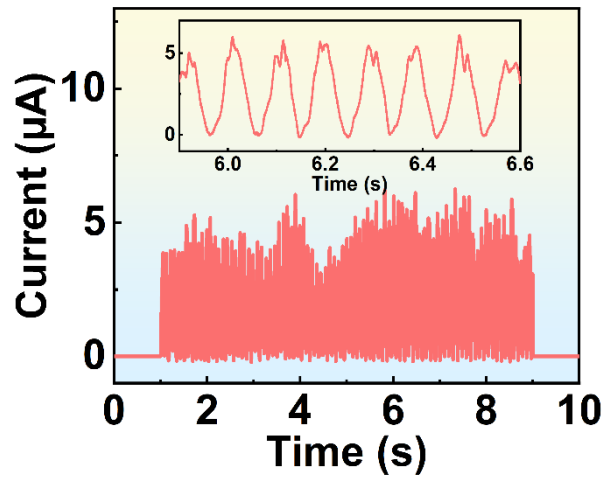


Figure S8. Short-circuit current of the MPS-TENG (n-Si). Inset: Partial magnified view of the current.

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